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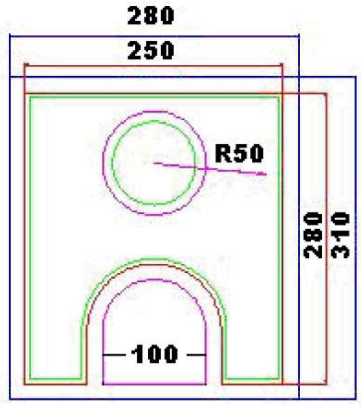
Data Sheet

LED Chip blue EOLC-470-34

Rev. 05, 2020

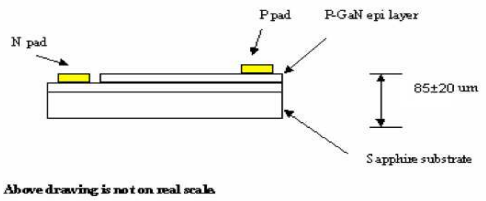
Radiation	Type	Electrodes
blue	GaN / sapphire	P + N up



All sizes in µm

Description

- Substrate: sapphire, epitaxial layer: GaN based material
- N bonding pad electrode: Au alloy
- P bonding pad electrode: Au alloy



Maximum Ratings

T_{amb}= 25°C, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward current (DC)		I_F			20	mA
Peak forward current	$t_p \leq$ 50 µs, t_p/T=½	I_{FM}			100	mA

Optical and Electrical Characteristics

T_{amb}= 25°C, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward voltage	I_F=20 mA	V_F		3.3	3.5	V
Reverse current	V_R=5 V	I_R			1	µA
Luminous intensity*	I_F=20 mA	I_v	260	280	300	mcd
Dominant wavelength	I_F=20 mA	λ_D	467	470	473	nm
FWHM	I_F=20 mA	$\Delta\lambda_{0.5}$		30		nm

*Measured on bare chip on TO-18 header

Packing

Chips on adhesive film with wire-bond side top

Art. No. 112 109

RoHS COMPLIANT Pb Pb-Free

We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer.